# OM SENI

## AO3407A
## P-Channel Enhancement Mode Field Effect Transistor

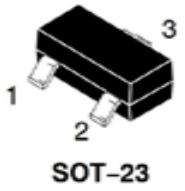
### General Description

The AO3407A/L uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications. *AO3407A and AO3407AL are electrically identical.*
*-RoHS Compliant*
*-AO3407AL is Halogen Free*

### Features

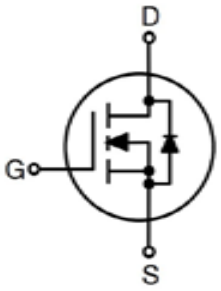
$V_{DS}$ (V) = -30V
$I_D$ = -4.3A ($V_{GS}$ = -10V)
$R_{DS(ON)}$ < 48mΩ ($V_{GS}$ = -10V)
$R_{DS(ON)}$ < 78mΩ ($V_{GS}$ = -4.5V)

***Rg,Ciss,Coss,Crss Tested***




SOT-23

1 – Gate
2 – Source
3 – Drain




**Absolute Maximum Ratings $T_A$=25°C unless otherwise noted**

| Parameter | | Symbol | Maximum | Units |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | -30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current [A,F] | $T_A$=25°C | $I_D$ | -4.3 | A |
| | $T_A$=70°C | | -3.5 | |
| Pulsed Drain Current [B] | | $I_{DM}$ | -20 | |
| Power Dissipation [A] | $T_A$=25°C | $P_D$ | 1.4 | W |
| | $T_A$=70°C | | 0.9 | |
| Junction and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to 150 | °C |

**Thermal Characteristics**

| Parameter | | Symbol | Typ | Max | Units |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient [AF] | t ≤ 10s | $R_{\theta JA}$ | 70 | 90 | °C/W |
| Maximum Junction-to-Ambient [A] | Steady-State | | 100 | 125 | °C/W |
| Maximum Junction-to-Lead [C] | Steady-State | $R_{\theta JL}$ | 63 | 80 | °C/W |

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**Electrical Characteristics ($T_J$=25°C unless otherwise noted)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **STATIC PARAMETERS** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $I_D$=-250μA, $V_{GS}$=0V | -30 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$=-30V, $V_{GS}$=0V | | | -1 | μA |
| | | $T_J$=55°C | | | -5 | |
| $I_{GSS}$ | Gate-Body leakage current | $V_{DS}$=0V, $V_{GS}$=±20V | | | ±100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$ $I_D$=-250μA | -1.5 | -2 | -2.5 | V |
| $I_{D(ON)}$ | On state drain current | $V_{GS}$=-10V, $V_{DS}$=-5V | -30 | | | A |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}$=-10V, $I_D$=-4.3A | | 39 | 48 | mΩ |
| | | $T_J$=125°C | | 55 | 68 | |
| | | $V_{GS}$=-4.5V, $I_D$=-3A | | 61 | 78 | mΩ |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$=-5V, $I_D$=-4.3A | | 11 | | S |
| $V_{SD}$ | Diode Forward Voltage | $I_S$=-1A,$V_{GS}$=0V | | -0.78 | -1 | V |
| $I_S$ | Maximum Body-Diode Continuous Current | | | | -2 | A |
| **DYNAMIC PARAMETERS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{GS}$=0V, $V_{DS}$=-15V, f=1MHz | | 668 | 830 | pF |
| $C_{oss}$ | Output Capacitance | | | 126 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 92 | | pF |
| $R_g$ | Gate resistance | $V_{GS}$=0V, $V_{DS}$=0V, f=1MHz | | 6 | 9 | Ω |
| **SWITCHING PARAMETERS** | | | | | | |
| $Q_g$ (10V) | Total Gate Charge (10V) | $V_{GS}$=-10V, $V_{DS}$=-15V, $I_D$=-4.3A | | 12.7 | 16 | nC |
| $Q_g$ (4.5V) | Total Gate Charge (4.5V) | | | 6.4 | | nC |
| $Q_{gs}$ | Gate Source Charge | | | 2 | | nC |
| $Q_{gd}$ | Gate Drain Charge | | | 4 | | nC |
| $t_{D(on)}$ | Turn-On DelayTime | $V_{GS}$=-10V, $V_{DS}$=-15V, $R_L$=3.5Ω, $R_{GEN}$=3Ω | | 7.7 | | ns |
| $t_r$ | Turn-On Rise Time | | | 6.8 | | ns |
| $t_{D(off)}$ | Turn-Off DelayTime | | | 20 | | ns |
| $t_f$ | Turn-Off Fall Time | | | 10 | | ns |
| $t_{rr}$ | Body Diode Reverse Recovery Time | $I_F$=-4.3A, dI/dt=100A/μs | | 22 | 30 | ns |
| $Q_{rr}$ | Body Diode Reverse Recovery Charge | $I_F$=-4.3A, dI/dt=100A/μs | | 15 | | nC |

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## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

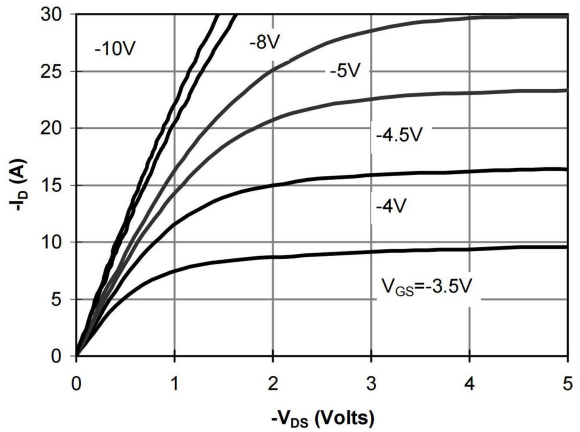



Figure 1: On-Region Characteristics

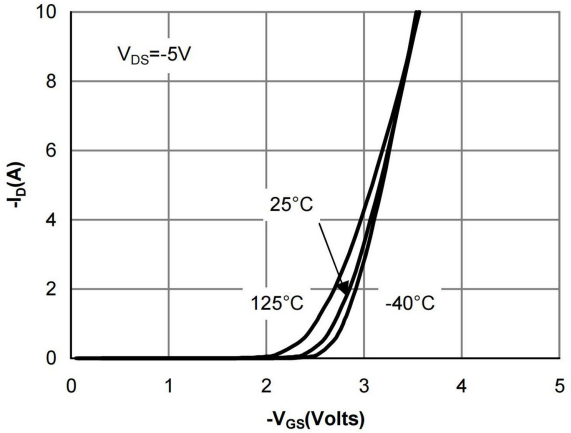



Figure 2: Transfer Characteristics

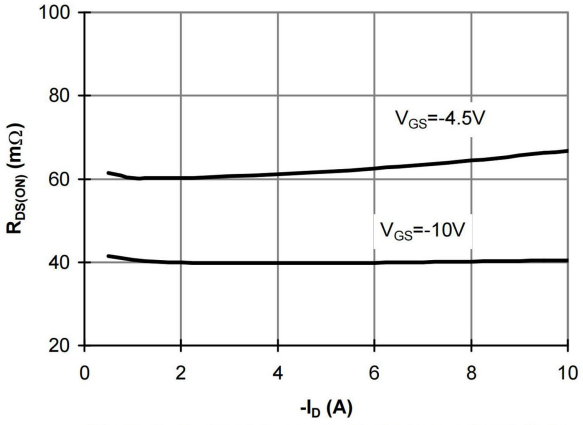



Figure 3: On-Resistance vs. Drain Current and Gate Voltage

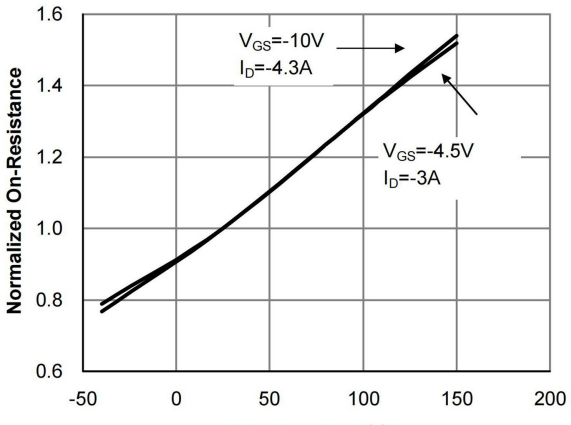



Figure 4: On-Resistance vs. Junction Temperature

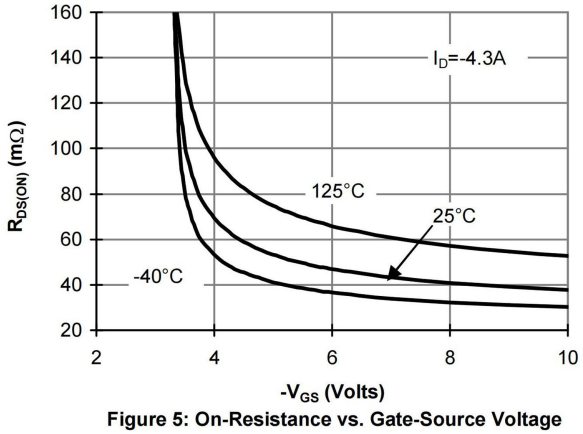



Figure 5: On-Resistance vs. Gate-Source Voltage

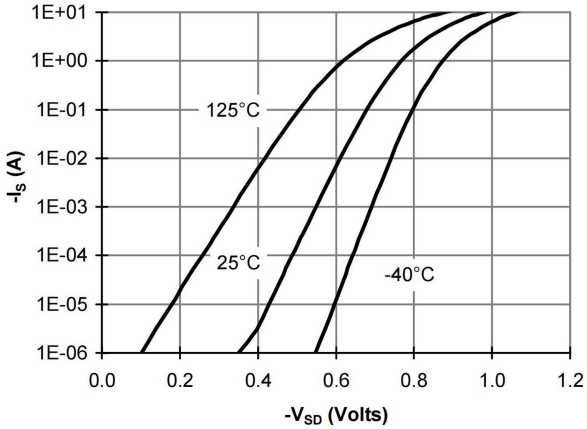



Figure 6: Body-Diode Characteristics

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## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

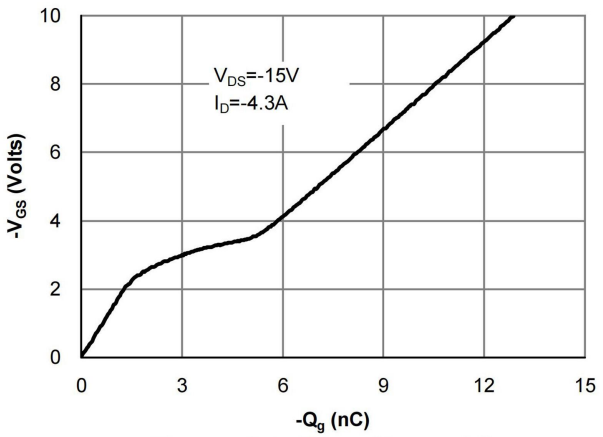



Figure 7: Gate-Charge Characteristics

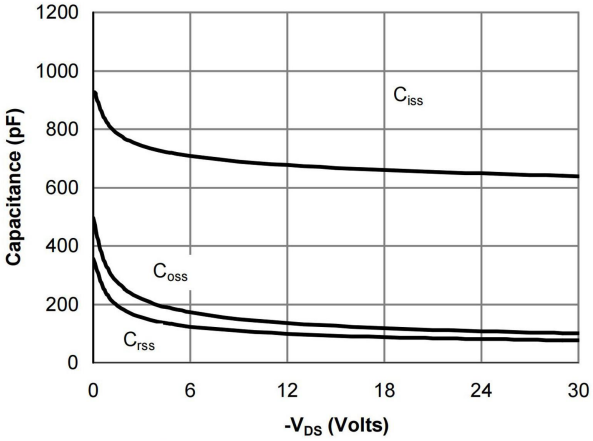



Figure 8: Capacitance Characteristics

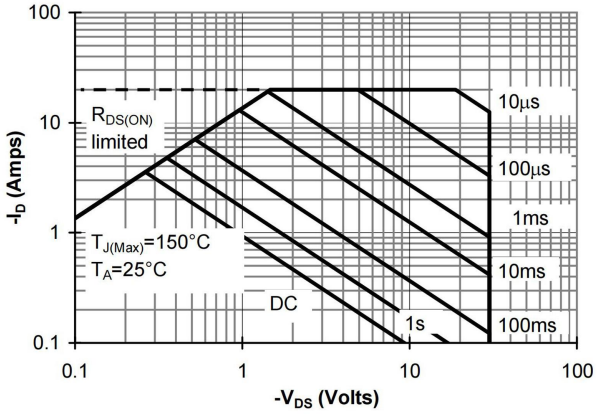



Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

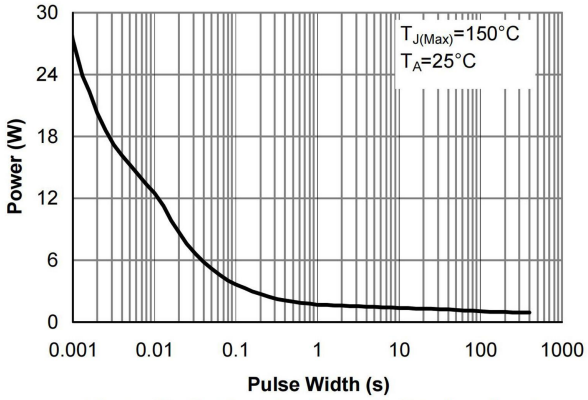



Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

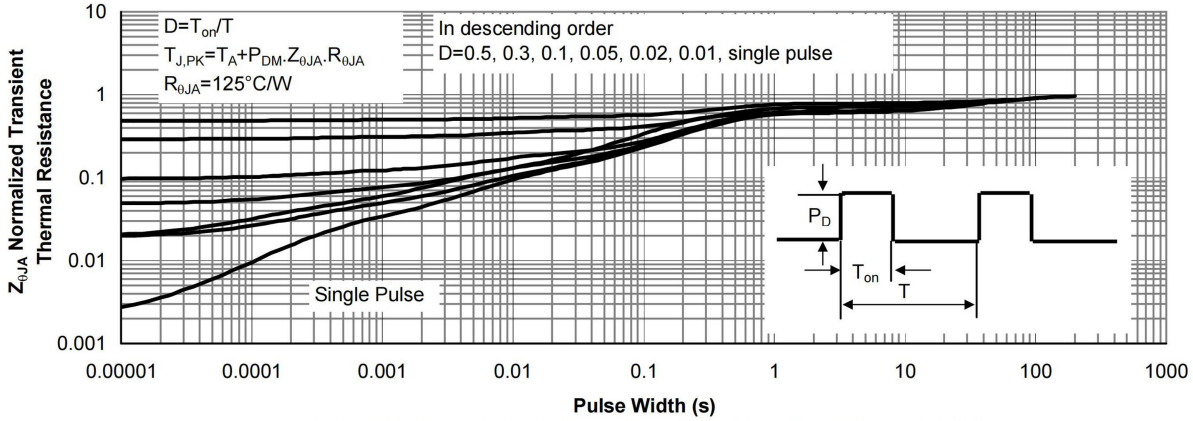


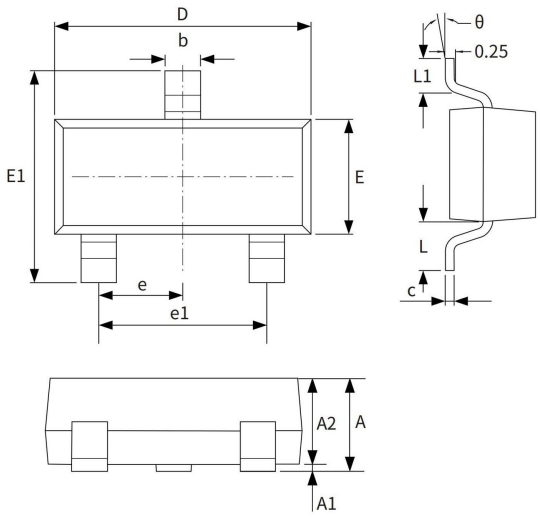

Figure 11: Normalized Maximum Transient Thermal Impedance(Note E)

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## Ordering Information

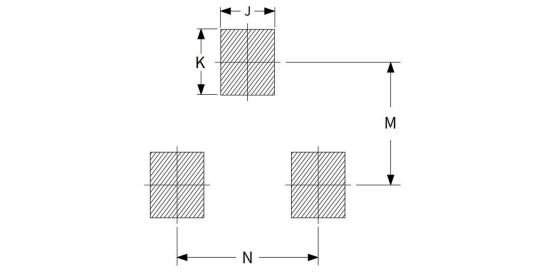
| PACKAGE | PACKAGE CODE | UNIT WEIGHT(g) | REEL(pcs) | BOX(pcs) | CARTON(pcs) | DELIVERY MODE |
|---|---|---|---|---|---|---|
| SOT-23 | R1 | 0.008 | 3000 | 30000 | 240000 | 7'' |

## Package Outline Dimensions (SOT-23)




| Symbol | Dimensions | | | |
|---|---|---|---|---|
| | Millimeters | | Inches | |
| | Min. | Max. | Min. | Max. |
| A | 0.90 | 1.15 | 0.035 | 0.045 |
| A1 | - | 0.10 | - | 0.004 |
| A2 | 0.90 | 1.05 | 0.035 | 0.041 |
| b | 0.30 | 0.50 | 0.012 | 0.020 |
| c | 0.10 | 0.20 | 0.004 | 0.008 |
| D | 2.80 | 3.00 | 0.110 | 0.118 |
| E | 1.20 | 1.40 | 0.047 | 0.055 |
| E1 | 2.25 | 2.55 | 0.089 | 0.100 |
| e | 0.950TYP | | 0.037TYP | |
| e1 | 1.80 | 2.00 | 0.071 | 0.079 |
| L | 0.550REF | | 0.022REF | |
| L1 | 0.30 | 0.50 | 0.012 | 0.020 |
| θ | - | 8° | - | 8° |

## Suggested Pad Layout




| Symbol | Dimensions | | | |
|---|---|---|---|---|
| | Millimeters | | Inches | |
| | Min. | Max. | Min. | Max. |
| J | 0.75 | 0.85 | 0.030 | 0.033 |
| K | 0.85 | 0.95 | 0.033 | 0.037 |
| M | 1.95 | 2.05 | 0.077 | 0.081 |
| N | 1.85 | 1.95 | 0.073 | 0.077 |